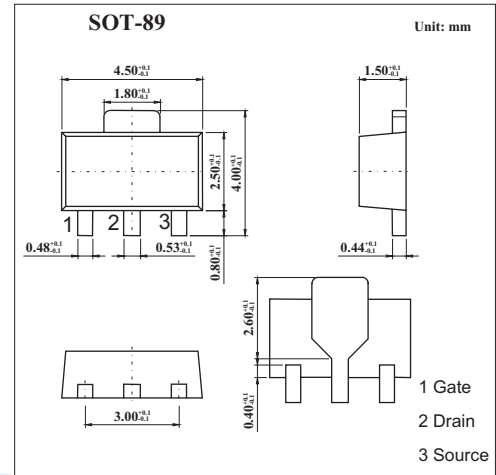


## P-Channel MOS Silicon FET

### 2SJ287

#### ■ Features

- Low on resistance
- Very high-speed switching
- Low-voltage drive



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V <sub>GS</sub> =0	V <sub>DSS</sub>	-30	V
Gate to source voltage V <sub>DS</sub> =0	V <sub>GSS</sub>	± 15	V
Drain current (DC)	I <sub>D</sub>	-500	m A
Drain current(pulse) *	I <sub>D</sub>	-2	A
Power dissipation	P <sub>D</sub>	3.5	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 μs; d ≤ 1%.

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit	
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0			-100	μ A	
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =± 12V, V <sub>DS</sub> =0			± 10	μ A	
Gate cut-off voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.0		-2.0	V	
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-250mA	240	400		ms	
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-250mA		1.5	2.2	Ω	
		V <sub>GS</sub> =-4V, I <sub>D</sub> =-250mA		2.2	3.3	Ω	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0, f=1MHZ		50		pF	
Output capacitance	C <sub>oss</sub>			35		pF	
Reverse transfer capacitance	C <sub>rss</sub>			10		pF	
Turn-on delay time	t <sub>d(on)</sub>				7		ns
Rise time	t <sub>r</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-250mA R <sub>L</sub> =60 Ω		10		ns	
Turn-off delay time	t <sub>d(off)</sub>				35		ns
Fall time	t <sub>f</sub>				20		ns

#### ■ Marking

Marking	JD
---------	----